
2SA1485

Silicon PNP Epitaxial

HITACHI

ADE-208-1020 (Z)

1st. Edition

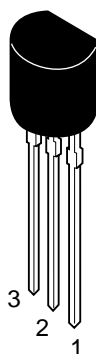
Mar. 2001

Application

Low frequency amplifier

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

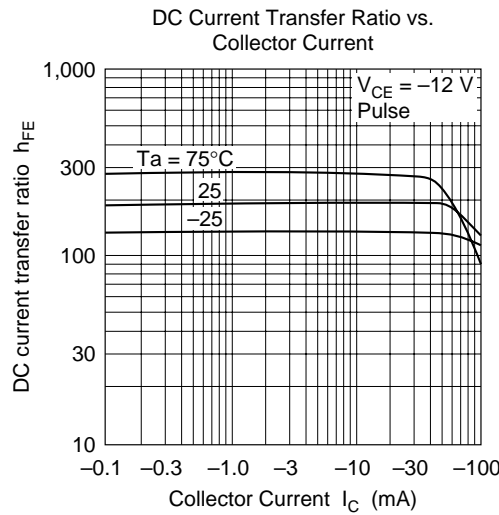
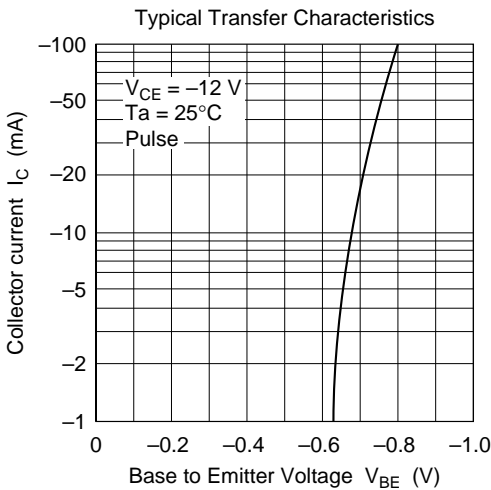
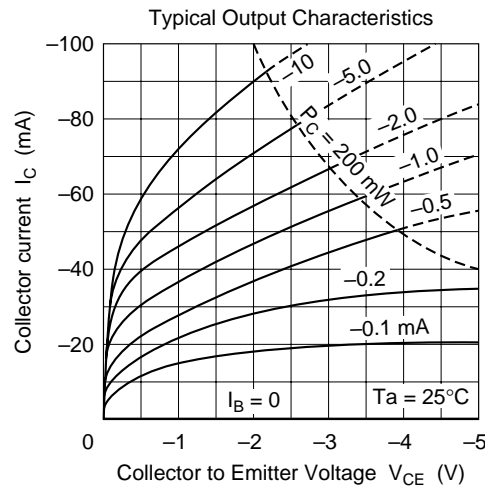
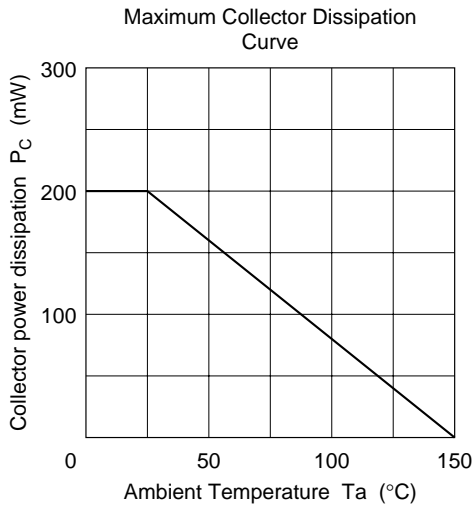
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

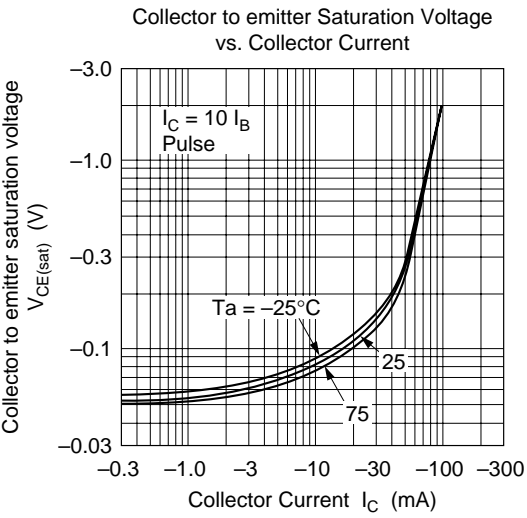
| Item | Symbol | Ratings | Unit |
|------------------------------|------------------|-------------|------------------|
| Collector to base voltage | V_{CBO} | -200 | V |
| Collector to emitter voltage | V_{CEO} | -200 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Collector current | I_{C} | -100 | mA |
| Collector power dissipation | P_{C} | 200 | mW |
| Junction temperature | T_{j} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|-----------------------------|------|-----|------|---------------|---|
| Collector to base breakdown voltage | $V_{(\text{BR})\text{CBO}}$ | -200 | — | — | V | $I_{\text{C}} = -10\ \mu\text{A}$, $I_{\text{E}} = 0$ |
| Collector to emitter breakdown voltage | $V_{(\text{BR})\text{CEO}}$ | -200 | — | — | V | $I_{\text{C}} = -0.5\ \text{mA}$, $R_{\text{BE}} = \infty$ |
| Emitter to base breakdown voltage | $V_{(\text{BR})\text{EBO}}$ | -5 | — | — | V | $I_{\text{E}} = -10\ \mu\text{A}$, $I_{\text{C}} = 0$ |
| Collector cutoff current | I_{CEO} | — | — | -500 | μA | $V_{\text{CE}} = -200\ \text{V}$, $R_{\text{BE}} = \infty$ |
| DC current transfer ratio | h_{FE} | 100 | — | 250 | | $V_{\text{CE}} = -12\ \text{V}$, $I_{\text{C}} = -2\ \text{mA}^{*1}$ |
| Collector to emitter saturation voltage | $V_{\text{CE}(\text{sat})}$ | — | — | -0.5 | V | $I_{\text{C}} = -30\ \text{mA}$, $I_{\text{B}} = -3\ \text{mA}^{*1}$ |
| Base to emitter voltage | V_{BE} | — | — | -1.0 | V | $V_{\text{CE}} = -12\ \text{V}$, $I_{\text{C}} = -2\ \text{mA}^{*1}$ |

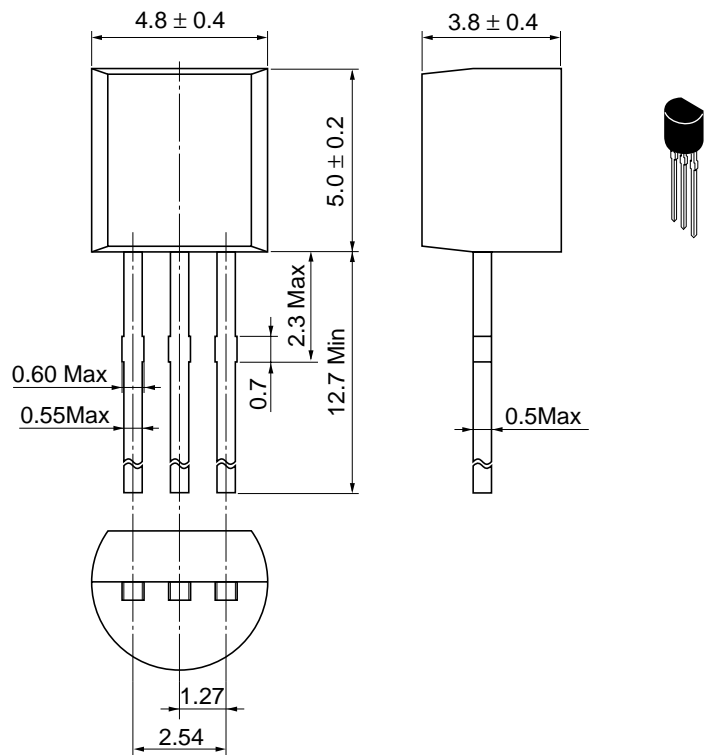
Note: 1. Pulse test





Package Dimensions

As of January, 2001
Unit: mm



| | |
|------------------------|-----------|
| Hitachi Code | TO-92 (1) |
| JEDEC | Conforms |
| EIAJ | Conforms |
| Mass (reference value) | 0.25 g |

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